L Number	Hits	Search Text	DB	Time stamp
1	10575	mixed adj2 oxide	USPAT;	2002/10/05 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	7645	doped adj2 oxide	USPAT;	2002/10/05 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	13425	doped near3 oxide	USPAT;	2002/10/05 15:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
22	16563	(dopant doped doping) near3 (oxide "Al.sub.2" adj "O.sub.3")	USPAT;	2002/10/05 15:20
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
29	53032	(dopant doped doping mixed) near5 (oxide "Al.sub.2" adj	USPAT;	2002/10/05 15:43
		"O.sub.3")	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
36	184465	(substrate deposit\$3 sputter\$4 cosputter\$4) near12	USPAT;	2002/10/05 16:02
	101100	("25. degree." "25" ((ambient room) adj (temperature temp))	US-PGPUB;	
		"20.degree." "20")	EPO; JPO;	
	,	20.degree. 20 j	DERWENT;	
			IBM TDB	
43	3514	((silicon adj monoxide) or SiO) near15 (sputter\$4 evaporat\$3	USPAT;	2002/10/05 15:24
43	3314	cosputter\$4 coevaporat\$3)	US-PGPUB;	2002/10/00 10:21
l			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
50	9169	((("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or sapphire)	USPAT;	2002/10/05 15:44
30	3103	with (source target)) or ((aluminum adj oxide) with (source	US-PGPUB;	2002, 10,00 10.11
		target))	EPO; JPO;	
		target//	DERWENT;	
			IBM_TDB	
57	12	(((silicon adj monoxide) or SiO) near15 (sputter\$4	USPAT;	2002/10/05 15:34
51	12	evaporat\$3 cosputter\$4 coevaporat\$3)) same (((("Al.sub.2"	US-PGPUB;	2002/10/00 10:04
		adj "O.sub.3") or Al2O3 or alumina or sapphire) with (source	EPO; JPO;	
1		target)) or ((aluminum adj oxide) with (source target)))	DERWENT;	
l		targetij or (talammam auj oxide) with (source targetij) j	IBM_TDB	
64	12349	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj	USPAT;	2002/10/05 15:42
U-7	12549	((dopant doped doping mixed) hears (oxide Al.sub.2 adj	US-PGPUB;	
İ		O.Sub.o // Samo (Smooth of Or)	EPO; JPO;	
			DERWENT;	
l			IBM TDB	
71	37	(((silicon adj monoxide) or SiO) near15 (sputter\$4	USPAT;	2002/10/05 15:35
11	31	evaporat\$3 cosputter\$4 coevaporat\$3)) and (((dopant doped	US-PGPUB:	2302/10/00 10:00
İ	;	doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) same	EPO; JPO;	
		(silicon or Si))	DERWENT;	
į		(Silicon of Sij)	IBM_TDB	
70	9000	((deport depot deping mixed) pears (exide "Al cub O" edi	USPAT;	2002/10/05 15:43
78	8632	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj		2002/10/05 15.43
i		"O.sub.3")) near15 (silicon or Si)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

85	2534	((substrate deposit\$3 sputter\$4 cosputter\$4) near12	USPAT;	2002/10/05 15:43
		("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and (((dopant doped doping mixed) near5	US-PGPUB; EPO; JPO;	
		((dopant doped doping finited) flears (oxide "Al.sub.2" adj "O.sub.3")) near15 (silicon or Si))	DERWENT;	
		(Oxide Alisabiz adj Oisabio // fical to (silicon of of))	IBM TDB	
99	7572	(Si silicon) near5 (dopant doped doping mixed) near5 (oxide	USPAT;	2002/10/05 15:44
		"Al.sub.2" adj "O.sub.3")	US-PGPUB;	
		•	EPO; JPO;	
ļ	İ		DERWENT;	
			IBM_TDB	
106	1554	(Si or silicon) near10 (dopant doped doping mixed) near10	USPAT;	2002/10/05 15:46
		(("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum	US-PGPUB;	
ŀ		adj oxide))	EPO; JPO; DERWENT;	
			IBM_TDB	
113	176	((substrate deposit\$3 sputter\$4 cosputter\$4) near12	USPAT;	2002/10/05 15:46
113	1,0	("25.degree." "25" ((ambient room) adj (temperature temp))	US-PGPUB;	2002. (0/00 (0/10)
		"20.degree." "20")) and ((Si or silicon) near10 (dopant doped	EPO; JPO;	
		doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or	DERWENT;	
		alumina or (aluminum adj oxide)))	IBM_TDB	
120	8	((substrate deposit\$3 sputter\$4 cosputter\$4) near12	USPAT;	2002/10/05 15:46
		("25.degree." "25" ((ambient room) adj (temperature temp))	US-PGPUB;	
		"20.degree." "20")) same ((Si or silicon) near10 (dopant	EPO; JPO;	
		doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or	DERWENT;	
00	328	Al2O3 or alumina or (aluminum adj oxide))) ((substrate deposit\$3 sputter\$4 cosputter\$4) near12	IBM_TDB USPAT;	2002/10/05 15:47
92	320	((Substrate deposits 3 sputters 2 cosputters 4) freat 12 ("25.degree." "25" ((ambient room) adj (temperature temp))	US-PGPUB;	2002/10/05 10:47
1	1	"20.degree." "20")) same (((dopant doped doping mixed)	EPO; JPO;	
		near5 (oxide "Al.sub.2" adj "O.sub.3")) near15 (silicon or Si))	DERWENT:	
}		,,,	IBM_TDB	
127	20636	(substrate deposit\$3 sputter\$4 cosputter\$4) near12	USPAT;	2002/10/05 16:01
1		("25 degree." ((ambient room) adj (temperature temp))	US-PGPUB;	
		"20.degree.")	EPO; JPO;	
			DERWENT;	
1.11		((Si or silicon) near10 (dopant doped doping mixed) near10	IBM_TDB USPAT;	2002/10/05 15:48
141	0	((Si of silicon) hear to (dopark doped doping mixed) hear to	US-PGPUB;	2002/10/03 13.40
		adj oxide))) same ((substrate deposit\$3 sputter\$4	EPO; JPO;	
ļ		cosputter\$4) near12 ("25.degree." ((ambient room) adj	DERWENT;	
		(temperature temp)) "20.degree."))	IBM TDB	
134	41	((Si or silicon) near10 (dopant doped doping mixed) near10	USPAT;	2002/10/05 15:48
ļ	ļ	(("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum	US-PGPUB;	
ļ		adj oxide))) and ((substrate deposit\$3 sputter\$4 cosputter\$4)	EPO; JPO;	
		near12 ("25.degree." ((ambient room) adj (temperature	DERWENT;	
140		temp)) "20.degree."))	IBM_TDB USPAT;	2002/10/05 15:56
148	1	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp))	US-PGPUB;	2002/10/03 10:00
		"20.degree.")) near20 (thermal adj budget)	EPO; JPO;	
}			DERWENT;	
			IBM_TDB	
155	589	(cool\$4 near3 (substrate wafer)) near20 ((substrate deposit\$3	USPAT;	2002/10/05 16:01
		sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room)	US-PGPUB;	
		adj (temperature temp)) "20 degree."))	EPO; JPO;	
			DERWENT;	
100		//downey downey downey arised \	IBM_TDB	2002/10/05 15:57
162	34	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) and ((cool\$4 near3 (substrate wafer)) near20	USPAT; US-PGPUB;	2002/10/05 15.5/
		((substrate deposit\$3 sputter\$4 cosputter\$4) near12	EPO; JPO;	
ļ		((substrate deposits sputters4 cosputters4) flear 12 ("25.degree." ((ambient room) adj (temperature temp))	DERWENT;	
		"20.degree."()))	IBM TDB	
169	3	I	USPAT;	2002/10/05 16:03
		deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree."	US-PGPUB;	
		((ambient room) adj (temperature temp)) "20 degree."))) and	EPO; JPO;	
		(applied adj materials).asn.	DERWENT;	
1	†		IBM_TDB	

176	70836	(deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25"	USPAT;	2002/10/05 16:07
		((ambient room) adj (temperature temp)) "20.degree." "20")	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
183	717		USPAT;	2002/10/05 16:05
		((ambient room) adj (temperature temp)) "20.degree." "20"))	US-PGPUB;	
		and (applied adj materials).asn.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
190	76	1 ///	USPAT;	2002/10/05 16:05
		"25" ((ambient room) adj (temperature temp)) "20.degree."	US-PGPUB;	
		"20")) and (applied adj materials).asn.) and ((dopant doped	EPO; JPO;	}
		doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3"))	DERWENT;	
			IBM_TDB	
197	107		USPAT;	2002/10/05 16:05
		("25.degree." ((ambient room) adj (temperature temp))	US-PGPUB;	
		"20.degree.")) and (applied adj materials).asn.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	00004404054005
204	18		USPAT;	2002/10/05 16:05
		("25.degree." ((ambient room) adj (temperature temp))	US-PGPUB;	
		"20.degree.")) and (applied adj materials).asn.) and ((dopant	EPO; JPO;	
		doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3"))	DERWENT;	
	1001	(IBM_TDB	2002/10/05 16:07
211	1224	(sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room)	USPAT;	2002/10/05 16:07
		adj (temperature temp)) "20.degree.")	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
040	50	//	IBM_TDB	2002/10/05 16:09
218	56		USPAT; US-PGPUB;	2002/10/03 10:09
		room) adj (temperature temp)) "20.degree.")) near20	EPO; JPO;	
		(necessary conventional conventionally typical essential		
		beneficial beneficially typically)	DERWENT;	
	•	1	IBM TDB	1